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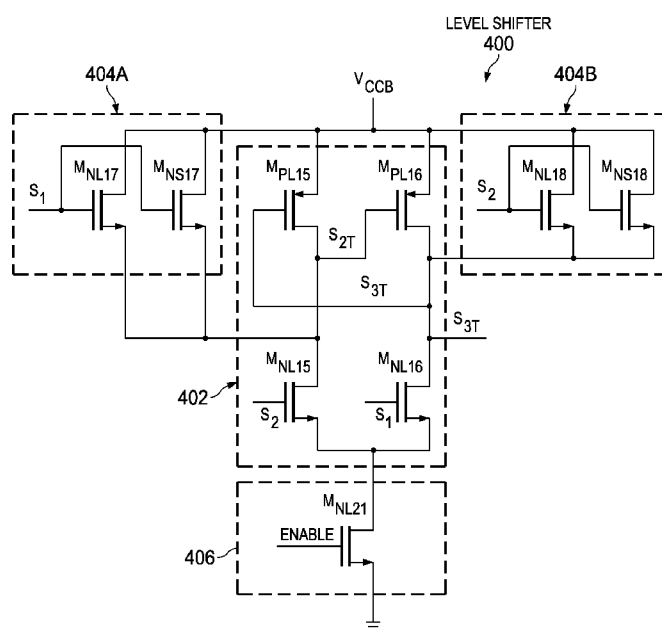


FIG. 4

(57) Abstract: A level shifter (400) is coupled to receive first and second input control signals (S_1 , S_2) and to provide an output control signal (S_{3T}). The level shifter (400) includes a level-shifting circuit (402) that has a first and a second PMOS transistor (M_{PL15} , M_{PL16}) and a first and a second NMOS transistor (M_{NL15} , M_{NL16}). A third NMOS transistor (M_{NL17}) is coupled between an upper rail (V_{CCB}) and the drain of the first PMOS transistor (M_{PL15}), with the gate of the third NMOS transistor (M_{NL17}) being controlled by the first input control signal (S_1). A fourth NMOS transistor (M_{NL18}) is coupled between the upper rail (V_{CCB}) and the drain of the second PMOS transistor (M_{PL16}), with the gate of the fourth NMOS transistor (M_{NL18}) being controlled by the second input control signal (S_2).



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LEVEL SHIFTER FOR A WIDE LOW-VOLTAGE SUPPLY RANGE

[0001] This relates generally to level shifters, and more particularly to a level shifter for a wide low-voltage supply range.

BACKGROUND

[0002] As supply voltage continues to drop for advanced microcontrollers, a need exists for low voltage circuits, such as translator products, that will allow these devices to reliably interface with legacy systems. These low voltage translators, in turn, must be capable of supporting a wide voltage range for maximum application flexibility. Existing products support a voltage range from 0.8 V to 3.6 V. However, even lower operating voltages are planned for the future.

SUMMARY

[0003] Described embodiments provide a level shifter that contains a boost circuit to overcome delays caused by the adjustments for the wide voltage supply range and provide a faster switching response. The boost circuit includes small NMOS transistors that work as pull-up helpers in parallel with the PMOS transistors in the level shifter. The NMOS helper transistors have their gates driven with the input voltage signals and their effectiveness scales with the input and output voltage levels.

[0004] In one aspect, an embodiment of a level shifter includes a level-shifting circuit coupled to receive first and second input control signals and to provide an output control signal, the level-shifting circuit comprising a first P-type metal oxide silicon (PMOS) transistor and a second PMOS transistor, a first N-type metal oxide silicon (NMOS) transistor and a second NMOS transistor; a third NMOS transistor coupled between an upper rail in a first voltage domain and the drain of the first PMOS transistor, the gate of the third NMOS transistor being controlled by the first input control signal; and a fourth NMOS transistor coupled between the upper rail and the drain of the second PMOS transistor, the gate of the fourth NMOS transistor being controlled by the second input control signal.

[0005] In another aspect, an embodiment of a voltage translator is coupled to translate an input signal received in a first voltage domain (VCCA) to an output signal provided in a second voltage domain (VCCB), wherein each of the first and second voltage domains can span a wide

range of low voltages. The voltage translator includes an input buffer coupled to receive the input signal and to provide a first input control signal and a second input control signal, the input buffer operating in the first voltage domain; a level shifter coupled to receive the first and second input control signals and to provide an output control signal; a gate control circuit coupled to receive the first and second input control signals and the output control signal and to provide a first gate control signal and a second gate control signal; and an output buffer coupled to receive the first gate control signal and the second gate control signal and to provide the output signal, wherein the level shifter, the gate control circuit and the output buffer each operate in the second voltage domain, the level shifter comprising: a level-shifting circuit comprising a first P-type metal oxide silicon (PMOS) transistor and a second PMOS transistor, a first N-type metal oxide silicon (NMOS) transistor and a second NMOS transistor; a third NMOS transistor coupled between an upper rail and the drain of the first PMOS transistor, the gate of the third NMOS transistor being controlled by the first input control signal; and a fourth NMOS transistor coupled between the upper rail and the drain of the second PMOS transistor, the gate of the fourth NMOS transistor being controlled by the second input control signal.

BRIEF DESCRIPTION OF THE DRAWINGS

- [0006] FIG. 1 depicts an example of an output buffer according to an embodiment.
- [0007] FIG. 2 depicts an implementation of an input buffer according to an embodiment.
- [0008] FIG. 3 depicts an implementation of a gate control circuit according to an embodiment.
- [0009] FIG. 3A depicts an implementation of a gate control circuit according to an embodiment.
- [0010] FIG. 4 depicts an implementation of a level shifter according to an embodiment.
- [0011] FIG. 5A illustrates the effects of the added helper transistors on output control signals S_{3T} and S_{2T} according to an embodiment.
- [0012] FIG. 5B illustrates the increased amplitude of V_{OUT} as one of the effects of the added helper transistors according to an embodiment.
- [0013] FIG. 6 depicts a schematic of a voltage translator according to an embodiment.
- [0014] FIG. 7 depicts a schematic of a conventional voltage translator.
- [0015] FIG. 8A depicts a set of signals when the voltage translator of FIG. 7 is operated with standard V_T transistors and an input signal operating at 0.8 V is to be translated to an output signal operating at 3.6 V.

[0016] FIG. 8B depicts a set of signals when the voltage translator of FIG. 7 is operated with low V_T transistors and an input signal operating at 0.6 V is to be translated to an output signal operating at 3.6 V.

[0017] FIG. 9 depicts an output buffer that could be used to handle the wide voltage supply range.

[0018] FIG. 10 depicts an embodiment of a conventional NAND/NOR pre-driver.

DETAILED DESCRIPTION OF EXAMPLE EMBODIMENTS

[0019] In the drawings, like references indicate similar elements. In this description, the term "couple" or "couples" means either an indirect or direct electrical connection unless qualified as in "communicably coupled" which may include wireless connections. Thus, if a first device couples to a second device, that connection may be through a direct electrical connection, or through an indirect electrical connection via other devices and connections.

[0020] The described embodiments evolved from a need to extend the lower voltage range of an existing voltage translator while maintaining support for the existing voltage range of the current device. FIG. 7 is a diagram of a conventional voltage translator 700. Voltage translator 700 receives a signal V_{IN} , which is operable in a first voltage domain, and translates signal V_{IN} to an output signal V_{OUT} , which is operable in a second voltage domain. For the purposes of this description, the first voltage domain has an upper rail designated by V_{CCA} and the second voltage domain has an upper rail designated by V_{CCB} . In the drawings, the lower rail for both the first and second voltage domains is shown as ground; having each of the lower rails equal to ground is not a requirement.

[0021] Voltage translator 700 contains four main elements: input buffer 702, level shifter 704, a pre-driver 706, which is shown in the drawing as a NAND-NOR pre-driver, and output buffer 708. Input buffer 702 operates within the first voltage domain, which uses upper rail V_{CCA} . Level shifter 704 operates in the second voltage domain, which uses V_{CCB} , but receives control signals V_{IN1} , V_{IN2} , which are generated in the first voltage domain. Pre-driver circuit 706 and output buffer 708 each operate in the second voltage domain. Voltage translator 700 supports a voltage range of 1.1-3.6 V and allows each upper rail V_{CCA} , V_{CCB} to assume any allowed value within this range. In at least one embodiment, voltage translator 700 is bi-directional, i.e., while the circuits shown translate signals from the voltage domain that uses V_{CCA} to the voltage domain that uses V_{CCB} , a second copy of this circuit operates to translate signals from the voltage

domain that uses V_{CCB} to the voltage domain that uses V_{CCA} . One or more pins on the circuit allow the selection of the desired direction of operation. Because of this bi-directionality, both of the output ports must be able to be placed into a high-impedance mode. In order to support lower voltages, both those currently in use and those planned for the future, changes to the circuit of voltage translator 700 are necessary to support a desired voltage range of 0.65-3.6 V. Individual elements of modules 702-708 are described herein in detail in conjunction with the modifications made to each module.

Parallel V_T Architecture:

[0022] A major problem that arises from the support of a wide voltage range is finding complementary metal oxide silicon (CMOS) devices that allow for optimal circuit design architectures. For example, a chip according to the embodiment of FIG. 7 was implemented using standard V_T transistors having threshold voltages equal to about 700 mV and operated at voltages that range from 1.1 V to 3.6 V. A test of this chip operating at 0.8 V is shown in FIG. 8A, which depicts the signals V_{IN} , V_{OUT} , V_{INT2} , V_{INT3} , V_{IN1} and V_{IN2} . The input buffer is switching from 0 V to 0.8 V, but signals V_{INT2} , V_{INT3} , produced in the level shifter, do not switch properly. This lack of switching in the level shifter is due to the fact that the V_T of the standard V_T transistors is very close to the upper voltage rail, so that the transistors did not have the headroom to properly turn on. As a result, output signal V_{OUT} is not being pulled either high or low.

[0023] The circuit of FIG. 7 was then simulated using low V_T transistors having a threshold voltage of about 300 mV throughout the circuit. FIG. 8B again depicts the signals V_{IN} , V_{OUT} , V_{INT2} , V_{INT3} , V_{IN1} and V_{IN2} . In this simulation, V_{OUT} operated properly and provided a good response to the changes in signal level of V_{IN} . However, other problems arise from the use of low V_T transistors, as low V_T transistors have greater leakage problems. This issue can be exacerbated when a need also exists to support a wide range of voltages, as in this description.

[0024] Table 1 and Table 2 below depict two implementations of the circuit of voltage translator 700 with low voltage transistors having two different widths. Table 1 depicts the PMOS, low threshold voltage (PCH_LVT) transistors, which are trying to pull the output voltage V_{OUT} high. V_{OH} is the output voltage high level and I_{OH} is the output drive requirement. V_{CC} designates the voltage domain of the output voltage and Spec indicates that the output voltage must remain above the specified value on a "HIGH" value in order for the output to fall with

specifications. Actual voltage values achieved during testing are provided for the PCH_LVT transistors, first with transistors having a width of 650 microns and second with transistors having a width of 1200 microns. Three values are given for each transistor width and indicate process and temperature: N/27C indicates nominal models at 27 degrees C; W/40C indicates weak models at 40 degrees C and W/125C indicates weak models at 125C. The PMOS transistors having a width of 650 microns were sized initially to allow the circuit to operate at 0.8 V. However, at this width, the circuit was not able to support operation in the other voltage domains; the entries highlighted in bold below each fell below the value allowed by the specifications.

[0025] Similarly, Table 2 depicts the N-channel, low threshold voltage (NCH_LVT) transistors, which are trying to pull the output voltage V_{OUT} low. Here, Spec indicates that the output voltage must remain below the specified value on a “LOW” value in order for the output to fall with specifications. The NMOS transistors are also shown with two widths: 200 microns and 400 microns. The NMOS transistors having a width of 200 microns were also sized initially to allow the circuit to operate at 0.8 V. Again the circuit was not able to support operation in the other voltage domains, as exemplified by the entries highlighted in bold, which fall below the value allowed by the specifications.

Table 1

VOH			PCH_LVT=650			PCH_LVT=1200		
VCC (V)	IOH (mA)	Spec (V)	N / 27C	W / - 40C	W / 125C	N / 27C	W / - 40C	W / 125C
0.8	1	0.6	0.684	0.664	0.607	0.74	0.732	0.705
1.1	3	0.85	0.84	0.833	0.642	0.969	0.969	0.89
1.4	6	1.05	0.967	0.982	0.58	1.186	1.196	1.055
1.65	8	1.2	1.15	1.182	0.75	1.4	1.417	1.253
2.3	9	1.75	1.881	1.917	1.648	2.081	2.099	1.97
3	12	2.3	2.521	2.561	2.29	2.748	2.768	2.633

Table 2

VOL			NCH_LVT=200			NCH_LVT=400		
VCC (V)	IOL (mA)	Spec (mV)	N / 27C	W / - 40C	W / 125C	N / 27C	W / - 40C	W / 125C
0.8	1	200	107	103	189	52	49	88
1.1	3	250	250	228	454	119	108	201
1.4	6	350	433	387	806	203	183	341
1.65	8	450	522	466	939	246	223	407
2.3	9	550	484	438	787	235	214	373
3	12	700	592	540	932	289	265	448

[0026] The widths of both the NMOS transistors and the PMOS transistors were then increased until operation in all of the allowed voltage domains fell within the specifications, as demonstrated by the voltage values shown. The smallest widths at which operation across the entire voltage range could be reached was 1200 microns for the PMOS transistors and 400 microns for the NMOS transistors. Although the voltage specifications could be met with these values, all of the transistors were oversized in order to meet the wide range of voltages. Such oversized transistors not only take up a large amount of real estate on a chip, but also produce output leakage that is far too high to be either desirable or competitive. Therefore, simply replacing all of the transistors in voltage translator 700 with low V_T transistors was not a viable solution.

[0027] Another possible solution to extend the voltage range is to stack several low V_T transistors in series in the output buffer. The problem in the circuit arises from the fact that while low V_T transistors are required by this circuit, the low V_T transistors must still be able to handle 3.6 V. Stacking the low V_T transistors allows each of these transistors to have a lower breakdown voltage (V_{DS}), since neither transistor is exposed to the entire voltage range. Subjecting the transistors to lower voltages allows for the use of smaller transistors, which in turn have less leakage. Using this configuration, FIG. 9 depicts output buffer 900, which includes two PMOS transistors M_{P1} and M_{P2} stacked in series between upper rail V_{CCB} and the output node V_{OUT} , with resistor R_5 coupled in series between transistors M_{P1} , M_{P2} and output node V_{OUT} . Two NMOS transistors M_{N1} and M_{N2} are stacked in series between the lower rail and the output node V_{OUT} , with resistor R_6 coupled in series between transistors M_{N1} , M_{N2} and output node V_{OUT} . The two PMOS transistors M_{P1} , M_{P2} are each controlled by gate control

signal V_P and the two NMOS transistors M_{N1} , M_{N2} are each controlled by gate control signal V_N . Gate control signals V_P and V_N are both provided by the gate drive control circuit. Applicant has determined that while the configuration of output buffer 900 is operable, this configuration would require a more complex circuit design for the gate drive control circuit and would also add more risk to high voltage and high temperature reliability.

[0028] In description hereinbelow, the transistors are numbered according to the following notation. For a transistor M_{XYZ} , X has a value of either N or P and indicates whether the transistor is NMOS or PMOS; Y has a value of either S or L and indicates whether the transistors has a standard threshold voltage or a low threshold voltage; and Z has a numerical value that distinguishes the transistor from similar transistors. The described embodiments were formed using proprietary processes that set a standard V_T at 700 mV and a low threshold voltage at 300 mV. However, the described embodiments are not limited by this proprietary process and other values of standard and low threshold voltages can also be used.

[0029] FIG. 1 depicts an example of an output buffer for a voltage translator according to an embodiment. Output buffer 100 operates in the second voltage domain, which in the embodiment shown uses upper rail V_{CCB} . PMOS transistors, M_{PL1} and M_{PS1} are coupled in parallel with each other between the upper rail V_{CCB} and a signal line that provides V_{OUT} . NMOS transistors, M_{NL1} and M_{NS1} are coupled in parallel with each other between the lower rail and the signal line that provides V_{OUT} . PMOS transistor M_{PL1} and NMOS transistor M_{NL1} are each low V_T transistors and are sized to handle voltages under 1 V, while PMOS transistor M_{PS1} and NMOS transistor M_{NS1} are each standard V_T transistors and are sized to handle voltage equal to or greater than 1 V. This differential sizing between standard V_T transistors and low V_T transistors generally extends across example embodiments. However, sizing for other voltage ranges can be used with example embodiments. Each of PMOS transistors, M_{PL1} , M_{PS1} are controlled by gate control signal V_P and each of NMOS transistors, M_{NL1} , M_{NS1} are controlled by gate control signal V_N ; both of the control signals are received from the pre-driver circuit. Additionally, resistor R_1 is coupled between PMOS transistor M_{PL1} and output signal V_{OUT} ; resistor R_2 is coupled between transistor M_{PS1} and output signal V_{OUT} ; resistor R_3 is coupled between transistor M_{NL1} and output signal V_{OUT} ; and resistor R_4 is coupled between transistor M_{NS1} and output signal V_{OUT} .

[0030] As described hereinbelow for the pre-driver circuit, gate control signals V_P and V_N can never be ON at the same time. In operation, when gate control signal V_P is low, PMOS transistors M_{PL1} and M_{PS1} are turned ON and operate together to pull output voltage V_{OUT} high. When gate control signal V_P is high, PMOS transistors M_{PL1} and M_{PS1} are OFF and allow output voltage V_{OUT} to be pulled low. As gate control signal V_P drops, low V_T PMOS transistor M_{PL1} will turn ON first and provide a quick response. Standard V_T PMOS transistor M_{PS1} turns ON only when gate control signal V_P is greater than 1 V, but can handle the larger currents necessary at the higher voltages. Similarly, when gate control signal V_N is high, NMOS transistors M_{NL1} and M_{NS1} turn ON and operate together to pull output voltage V_{OUT} low. Low V_T transistor M_{NL1} will turn ON first and provide a quick response. Standard V_T transistor M_{NS1} turns ON only when the input voltages are greater than or equal to 1 V, but can handle the larger currents necessary at the higher voltages.

[0031] Tables 3 and 4 below provide similar information to that given in Tables 1 and 2, but show the operational voltages for an embodiment in which gates of low V_T PMOS transistors have widths of 400 microns and lengths of 0.4 microns; standard V_T transistors have gate widths of 800 microns. The gates of the low V_T NMOS transistors are 150 microns wide and 1.7 microns long, while the gates of the standard V_T NMOS transistors are 200 microns wide. As shown in these tables, all levels of operation are within specification.

Table 3

VOH			PCH_LVT=400, PCH=800		
VCC (V)	IOH (mA)	Spec (V)	N / 27C	W / - 40C	W / 125C
0.8	1	0.6	0.748	0.621	0.721
1.1	3	0.85	1.028	1.011	0.991
1.4	6	1.05	1.297	1.289	1.243
1.65	8	1.2	1.534	1.529	1.476
2.3	9	1.75	2.2	2.197	2.153
3	12	2.3	2.883	2.878	2.832

Table 4

VOL			NCH_LVT=150, NCH=200		
VCC (V)	IOL (mA)	Spec (mV)	N 27C	W / - 40C	W / 125C
0.8	1	200	70	133	169
1.1	3	250	97	114	183
1.4	6	350	145	143	250
1.65	8	450	168	160	278
2.3	9	550	154	145	237
3	12	700	186	178	277

[0032] The use of a parallel V_T architecture in applications that can receive a wide range of voltages is not limited to the example shown in FIG. 1. FIG. 2 depicts an input buffer 200 for the same voltage translator according to an embodiment. Input buffer 200 operates in the first voltage domain and includes two inverters 202, 204, which receive an input signal V_{IN} and provide input control signals S_1 and S_2 .

[0033] Inverter 202 includes PMOS low V_T transistor M_{PL2} coupled in series with NMOS low V_T transistor M_{NL2} between the upper rail V_{CCA} and the lower rail. PMOS standard V_T transistor M_{PS2} is coupled in series with NMOS standard V_T transistor M_{NS2} between the upper rail and the lower rail. Each of transistors M_{PL2} , M_{PS2} , M_{NL2} , and M_{NS2} , are coupled to receive input signal V_{IN} on a respective gate. The midpoint between low V_T transistors M_{PL2} and M_{NL2} is coupled to the midpoint between standard V_T transistors M_{PS2} and M_{NS2} to provide input control signal S_1 .

[0034] Inverter 204 includes PMOS low V_T transistor M_{PL3} coupled in series with NMOS low V_T transistor M_{NL3} between the upper rail and the lower rail. PMOS standard V_T transistor M_{PS3} is coupled in series with NMOS standard V_T transistor M_{NS3} between the upper rail and the lower rail. Each of transistors M_{PL3} , M_{PS3} , M_{NL3} and M_{NS3} are coupled to receive input control signal S_1 on a respective gate. The midpoint between low V_T transistors M_{PL3} and M_{NL3} is coupled to the midpoint between standard V_T transistors M_{PS3} and M_{NS3} to provide input control signal S_2 .

[0035] Using the described combination of low V_T transistors coupled in parallel with standard V_T transistors allows input buffer 200 and output buffer 100 to operate effectively across the entire range of voltages of 0.65 V to 3.6 V. The low V_T devices are sized for drive strength (i.e., current) requirements below 1 V operation while the standard V_T components are sized for the higher voltage drive strength requirements. The combination of low V_T transistors and standard

V_T transistors coupled in parallel minimizes the static leakage current while still supporting the full range of device operation. As described herein for the level shifter and pre-driver circuits, many of the transistors in these modules can be implemented with the described low V_T and standard V_T transistors coupled in parallel to allow operation across the larger range of voltages while optimizing the operation across the extended range.

[0036] The described configuration is advantageous in that this configuration allows a designer to have another degree of freedom in the circuit architecture, depending on the product requirements across the full operating voltage range. The transistor widths and lengths for both low V_T and standard V_T components can be selected separately and PMOS devices and NMOS devices can each be optimized. Circuits that work over a wider voltage range than existing devices are now possible.

Output Driver Gate Control Circuit

[0037] When designing an output buffer, it is critical to optimize the gate control circuit. This optimization is especially necessary when the output buffer is operated with tristate logic, i.e., the output buffer can be placed in a high impedance state where neither the PMOS pull-ups nor the NMOS pull-downs are enabled. High impedance is required, for example, in embodiments in which current flow can be bi-directional. As described hereinabove, the circuit of FIG. 7 can be implemented with two copies of voltage translator 700, one copy translating from the first domain to the second domain, the second copy translating from the second domain to the first domain. Only one of the two copies can be active at a time, yet the two copies share pins on the chip. Whenever an output buffer is not in use, that output buffer must be placed in a high impedance mode. Improper design of the gate control circuit can allow excess shoot-through current and corresponding ground noise if both output devices are enabled for a short period of time. One method of resolving this issue would be for the gate driver to turn ON the output devices slower to minimize the shoot-through current, but this would result in degraded propagation delay through the data path.

[0038] One existing solution, shown in FIG. 7, uses a NAND-NOR pre-driver 706 for outputs that can be placed in a high impedance state. FIG. 10 is an enlarged reproduction of pre-driver 706. Pre-driver 706 includes two separate circuits: NAND circuit 1002 provides gate control signal V_P and NOR circuit 1004 provides gate control signal V_N .

[0039] NAND circuit 1002 has two PMOS transistors M_{P3} , M_{P4} coupled in parallel between upper rail V_{CCB} and gate control signal V_P and two NMOS transistors M_{N3} , M_{N4} coupled in series between gate control signal V_P and the lower rail. Transistors M_{P3} and M_{N4} are each controlled by a first enable signal EN_1 and transistors M_{P4} and M_{N3} are each controlled by signal V_{INT3} , which is received from the level shifter circuit.

[0040] NOR circuit 1004 has two PMOS transistors M_{P5} , M_{P6} coupled in series between upper rail V_{CCB} and gate control signal V_N and two NMOS transistors M_{N5} , M_{N6} coupled in parallel between gate control signal V_N and the lower rail. Transistors M_{P5} and M_{N5} are each controlled by a second enable signal EN_2 and transistors M_{P6} and M_{N6} are each controlled by signal V_{INT3} from the level shifter circuit. In pre-driver 706, signal V_{INT3} provides a level-shifted version of the input signal to input buffer 702 and controls the value of gate control signals V_P and V_N to drive the transistors in output buffer 708. Enable signals EN_1 and EN_2 operate to ensure that when the output buffer is placed in high impedance mode, V_P is pulled high to turn OFF PMOS transistors M_{PL1} and M_{PS1} in output buffer 100 and V_N is pulled low to turn OFF NMOS transistors M_{NL1} , M_{NS1} . Enable signals EN_1 , EN_2 also ensure that the transistors in output buffer 100 are turned OFF during power-on procedures.

[0041] In adapting pre-driver circuit 706 to operate with an extended range of voltages, the majority of the transistors were each replaced by a low- V_T transistor coupled in parallel with a standard V_T transistor, as described herein in the section about parallel V_T architecture. However, due to the additional leakage that low V_T transistors have in relationship to standard V_T transistors (e.g., three orders of magnitude more), it was also considered desirable to eliminate transistors wherever possible to keep the leakage low and the area necessary for the circuit as small as possible.

[0042] FIG. 3 depicts a gate control circuit 300 according to an embodiment. Gate control circuit 300 is specifically designed to drive an output buffer that operates with tristate logic that can be placed in a high-impedance state. Gate control circuit 300 includes four sections: a gate isolation switch 302, pull-up circuit 304, pull-down circuit 306 and an enable/disable control circuit 308. Gate isolation switch 302 provides isolation of gate control signal V_P from gate control signal V_N when necessary but allows gate control signals V_P and V_N to share the pull-up circuit 304 and pull-down circuit 306 when the output buffer is enabled. This is in contrast to circuits 1002, 1004 of FIG. 10, where pull-up transistors and pull-down transistors are coupled to

control gate control signal V_P and additional pull-up transistors and pull-down transistors are coupled to control gate control signal V_N . Enable/disable control circuit 308 provides enable signals EN_1 , EN_2 , which ensure that gate control signals V_P and V_N can be placed in high impedance when necessary. Pull-up circuit 304 and pull-down circuit 306 use the parallel V_T architecture described hereinabove and provide additional helpers and enable signals as described hereinbelow.

[0043] Enable/disable control circuit 308 includes three inverters, coupled in parallel between upper rail V_{CCB} and the lower rail. Enable/disable control circuit 308 receives an input signal 310 and provides enable signals EN_1 and EN_2 . A first inverter includes PMOS transistor M_{P24} and NMOS transistor M_{N24} ; this first inverter receives input signal 310 and provides an inverted signal 312. A second inverter includes PMOS transistor M_{P25} and NMOS transistor M_{N25} , receives input signal 312 and provides the enable signal EN_1 . A third inverter includes PMOS transistor M_{P26} and NMOS transistor M_{N26} , receives enable signal EN_1 and provides enable signal EN_2 . In one embodiment, the enable/disable control circuit 308 is controlled by the settings applied to pins on a chip containing the described gate control circuit 300. In one embodiment, the value of input signal 310 is controlled by the direction of voltage translation and can also be set by an enable pin.

[0044] Gate isolation switch 302 is at the heart of gate control circuit 300 and includes two PMOS transistors M_{PL9} , M_{PS9} and two NMOS transistors M_{NL9} , M_{NS9} coupled in parallel between gate control signal V_P and gate control signal V_N . In accordance with the parallel V_T architecture, transistors M_{PL9} and M_{NL9} are low V_T transistors, which are selected to operate below 1V, while transistors M_{PS9} and M_{NS9} are standard V_T transistors, which are selected to operate above 1V. The two NMOS transistors M_{NL9} , M_{NS9} are controlled by a first enable signal EN_1 and the two PMOS transistors M_{PL9} , M_{PS9} are controlled by a second enable signal EN_2 . Gate isolation switch 302 connects the gate control signal V_P and gate control signal V_N when the output is enabled and disconnects the output signals when the output buffer is disabled, i.e. in the high impedance state. While gate isolation switch 302 is shown as containing both standard V_T transistors and low V_T transistors, this combination is not necessary in gate isolation switch 302. In another embodiment (not specifically shown) that does not span the wide range of the described embodiment, gate isolation switch 302 includes only a single NMOS transistor controlled by the first enable signal and a single PMOS transistor controlled by the second

enable signal. The use of gate isolation switch 302 in place of NAND/NOR gate drivers can reduce the total low V_T transistor width while maintaining consistent drive turn-on.

[0045] The output gate pull-up circuit 304 includes five transistors coupled in parallel between the upper rail, V_{CCB} , and gate control signal V_P . PMOS transistors M_{PL8} and M_{PS8} are the main pull-up transistors and are controlled by output control signal S_{3T} , which is received from the level shifter circuit and will drive the gate control signal V_P in response to the input signal received by the voltage translator. However, during development of the overall voltage translator, it was necessary to skew the sizes of the PMOS transistors in relationship to the NMOS transistors throughout the voltage translator. Because of this skewed relationship, helper NMOS transistors M_{NL7} and M_{NS7} are provided and are each controlled by input control signal S_1 , which is received from the input buffer 200. A description of the exact manner in which these helper NMOS transistors, M_{NL7} , M_{NS7} , operate to assist the main PMOS transistors, M_{PL8} , M_{PS8} is deferred to the section herein that describes the voltage shifter. Using both standard V_T transistors and low V_T transistors provides for optimal propagation delays across the entire voltage range, while the use of the NMOS helper transistors provides a supply boost where necessary. The final transistor in pull-up circuit 304 is PMOS transistor M_{PL12} , which is controlled by enable signal EN_1 . PMOS transistor M_{PL12} can be used during power-up of the circuit to pull gate control signal V_P high and turn the PMOS output transistors, M_{PL1} , M_{PL2} , OFF. This transistor can be implemented either as shown or using parallel low V_T and standard V_T transistors.

[0046] In a similar fashion, output gate pull-down circuit 306 includes five transistors coupled in parallel between gate control signal V_N and the lower rail. NMOS transistors M_{NL11} and M_{NS11} are the main pull-down transistors and are also controlled by output control signal S_{3T} from the level shifter circuit. Transistors M_{NL11} , M_{NS11} drive the gate control signal V_N in response to the input signal received by the voltage translator. Helper NMOS transistors M_{NL10} and M_{NS10} are provided and are each controlled by input control signal S_2 , which is also received from the input buffer 200. The use of one pair of NMOS transistors driven according to the first voltage domain and one pair of NMOS transistors driven according to the second voltage domain provides for optimal propagation delays across the entire voltage range. Further description of the operation of helper NMOS transistors, M_{NL10} , M_{NS10} is again deferred herein to the section that describes the voltage shifter. The final transistor in output gate pull-down circuit 306 is

NMOS transistor M_{NL12} , which is controlled by enable signal EN_2 . NMOS transistor M_{NL12} can be used during power-up of the circuit to pull gate control signal V_N low and turn the NMOS output transistors, M_{NL1} , M_{NL2} , OFF. As with transistor M_{PL12} , transistor M_{PL12} can be implemented either as shown or using parallel low V_T and standard V_T transistors.

[0047] When it is desirable to place the output buffer into a high impedance mode, input signal 310 can be used to set enable signal EN_1 at the lower rail and to set enable signal EN_2 at the upper rail. This setting turns ON PMOS transistor M_{PL12} to pull V_P high and turn OFF the PMOS transistors in output buffer 100; this setting also turns ON NMOS transistor M_{NL12} to pull V_N low and turn OFF the NMOS transistors in output buffer 100. At the same time, transistors M_{PL9} , M_{NL9} , M_{PS9} , M_{NS9} of gate isolation switch 302 are all turned OFF. During normal operation, enable signal EN_1 is set at the upper rail and enable signal EN_2 is set at the lower rail to turn OFF both PMOS transistor M_{PL12} and NMOS transistor M_{NL12} , allowing the other transistors in pull-up circuit 304 and pull-down circuit 306 to control the values of V_P and V_N . This setting also turns ON the switches in gate isolation switch 302. Although not specifically shown in FIG. 3, enable/disable control circuit 308 can also be implemented using the parallel architecture described earlier.

[0048] In contrast to the pre-driver circuit 706, which has been widely used in the past, the described pre-driver circuit only uses a pull-up device for the PMOS gate driver and a pull-down device for the NMOS gate driver along with the connecting transmission gate. The gate control circuit 300 effectively eliminates transistors M_{N4} and M_{P5} from the design, while combining the associated enable signals and additionally using the advantages of parallel V_T architecture and the helper transistors that assist across the wide voltage range. Using gate isolation switch 302, gate control circuit 300 provides a simpler control circuit from a timing perspective.

[0049] It should be noted that while the described gate isolation switch 302 was originally designed to operate with a wide range of voltages that called for the use of parallel V_T architecture, gate isolation switch 302 can also be implemented in circuits that do not use the parallel architecture. FIG. 3A depicts a gate control circuit 300A according to an embodiment. In this simplified embodiment, gate isolation switch 302A includes a PMOS transistor M_{P27} coupled in parallel with NMOS transistor M_{N27} between gate control signal V_P and gate control signal V_N . The gate of NMOS transistor M_{N27} is controlled by enable signal EN_1 and the gate of PMOS transistor M_{P27} is controlled by enable signal EN_2 . Pull-up circuit 304A can be

configured with a desired configuration of transistors coupled to both the upper rail and to gate control signal V_P . Similarly, pull-down circuit 306A can also be configured with a desired configuration of transistors coupled to both the lower rail and to gate control signal V_N . This simplified version of gate isolation circuit 302A can connect pull-up circuit 304A and gate control signal V_P to pull-down circuit 306A and gate control signal V_N when gate control circuit 300A is active, yet effectively close the connection when the output buffer controlled by gate control circuit 300A is placed in high impedance mode.

[0050] The described embodiments are advantageous because the gate isolation switch 302 inherently keeps the output in a high impedance state during power-up and provides a natural break-before-make feature due to the transmission gate. Accordingly, when gate control signal V_P goes from a high value to a low value, the charge on gate control signal V_P must discharge through gate isolation switch 302. Before that can occur, gate control signal V_N will first drop, turning OFF NMOS output transistors M_{NL1} , M_{NS1} . Only then can gate control signal V_P discharge through pull-down circuit 306. This connection simplifies the gate control circuit, minimizes the overall die area and minimizes the static leakage from the gate control circuit. In one embodiment, the use of gate isolation switch 302 provided the following advantages over the conventional NAND/NOR pre-driver configuration: gate isolation switch 302 is fifty percent smaller, has a 1.3% reduction in total static leakage current, and the propagation delay is 34.5% lower compared to the NAND/NOR circuit.

Level Shifter Boost Circuit

[0051] A challenging problem that arises as a result of expanding the voltage range of the voltage translator is designing level shifter 400 with sufficient transient response. As a general design rule, the width of the PMOS transistors is twice the width of the NMOS transistors, i.e., a 2:1 ratio. However, when the level shifter is operating to translate a signal from 0.65V to 3.6V, i.e., the maximum upwards level shift, the NMOS transistors are receiving an ON signal that is barely able to turn the NMOS transistors ON, while the PMOS transistors are receiving a much stronger signal. In order to work properly with this large voltage difference, the PMOS transistor widths must therefore be chosen to be significantly smaller than the NMOS transistor widths. In one embodiment, the resulting ratio between the PMOS and NMOS transistor widths is 1:3, i.e., the PMOS transistor are much smaller than usual. While this extreme skewing of transistor sizes is necessary when the input signal is low and the output signal is high, this skewing causes poor

transient response for low-to-high switching when the input signal is higher and closer to the voltage level of the output. The poor transient response in turn makes fast switching difficult to achieve.

[0052] One possible solution to the extreme skewing of sizes of the PMOS/NMOS transistors can be to use passive resistors coupled in parallel with the PMOS transistors to pull-up the output signal. However, these devices will contribute additional leakage current to the design when the output is driven low and will take up a significant amount of area since the resistors would necessarily have large resistance values.

[0053] FIG. 4 depicts a level shifter 400 that has been implemented according to an embodiment. Of the design shown, level shifting circuit 402 of level shifter 400 is the original level shifter as shown in FIG. 7, although in level shifting circuit 402, all of the previous transistors are replaced by low V_T transistors. Level shifting circuit 402 is made up of two PMOS transistors M_{PL15} , M_{PL16} and two NMOS transistors M_{NL15} , M_{NL16} . PMOS transistor M_{PL15} is coupled in series with NMOS transistor M_{NL15} between upper rail, V_{CCB} , and the lower rail and PMOS transistor M_{PL16} is coupled in series with NMOS transistor M_{NL16} between V_{CCB} and the lower rail. The gate of PMOS transistors M_{PL15} is coupled to the drain of PMOS transistor M_{PL16} and the gate of PMOS transistors M_{PL16} is coupled to the drain of PMOS transistor M_{PL15} . Finally, the gate of NMOS transistor M_{NL15} is controlled by input control signal S_2 and the gate of NMOS transistor M_{NL16} is controlled by input control signal S_1 ; both of input control signals S_1 and S_2 are created in the first voltage domain. This means that NMOS transistors M_{NL15} , M_{NL16} are controlled by signals created in the first voltage domain, while PMOS transistors M_{PL15} , M_{PL16} are controlled by signals in the second voltage domain, creating the problem noted above. Notably, only low V_T transistors are used for switching capability over the full voltage range from 0.65V to 3.6V on either supply. The width of low V_T transistors is minimized to keep the leakage current as low as possible.

[0054] Rather than providing passive resistors coupled in parallel with the PMOS transistors to pull-up the output signal, level shifter 400 discloses the use of several NMOS transistors coupled in parallel with the PMOS transistors as helper transistors. In the embodiment shown, pull-up circuit 404A includes two NMOS transistors, M_{NL17} , M_{NS17} , which are each coupled in parallel with PMOS transistor M_{PL15} between upper rail V_{CCB} and output control signal S_{3T} . The gates of NMOS transistors M_{NL17} , M_{NS17} are controlled by input control signal S_1 . A second pull-up

circuit 404B includes two additional NMOS transistors M_{NL18} , M_{NS18} , which are each coupled in parallel with PMOS transistor M_{PL16} between upper rail V_{CCB} and output control signal S_{2T} and have their gates controlled by input control signal S_2 . The size of these helper NMOS transistors M_{NL17} , M_{NS17} , M_{NL18} , M_{NS18} , is small compared to the size of NMOS transistors M_{NL15} , M_{NL16} . In one embodiment, the helper NMOS transistors M_{NL17} , M_{NS17} , M_{NL18} , M_{NS18} , have respective widths that are one-fifth to one-fourth the width of NMOS transistors M_{NL15} , M_{NL16} . Since the NMOS transistors are driven by the input control signals S_1 , S_2 , while the PMOS transistors are driven by output control signals S_{2T} , S_{3T} , the effectiveness of the pull-up circuits 404 scales with the input and output voltage levels. Accordingly, when the voltage of upper rail V_{CCA} is low, pull-up circuits 404 will only be weakly turned on. However, since the response of NMOS transistors M_{NL15} , M_{NL16} is weak in this same situation, a strong response from pull-up circuit 404 is not desired. When the voltage on upper rail V_{CCA} is set to be higher and the effect of the skewed sizes of the PMOS transistors M_{PL17} , M_{PL18} is very evident, the effect of pull-up circuits 404 is stronger and continues to scale upward as upper rail V_{CCA} is set to higher values. The pull-up circuits 404 help improve the switching time and data rate. A final element of level shifter 400 is a disable switch 406, which in the described embodiment contains a single low threshold voltage NMOS transistor M_{NL21} . Disable switch 406 is provided to reduce the dynamic current of the full bitcell by blocking current path of non-switching half bit level shifter. Accordingly, when the output buffer to which the level shifter is coupled is placed in high-impedance mode, the disable switch 406 will turn OFF to keep the level shifter from switching based on the input state. Although not implemented in parallel architecture in the embodiment shown, disable switch 406 could also be implemented in parallel in other embodiments. The width of the low V_T transistor is minimized to keep the leakage current as low as possible.

[0055] FIG. 5A illustrates the effects of the added helper transistors on the output control signals S_{3T} and S_{2T} in an implementation of the described level shifter 400. Each of signals S_{3T} , S_{2T} is shown both with and without the helper NMOS transistors. Use of the NMOS helpers allows output control signal S_{2T} to rise more quickly, thus turning off PMOS transistor M_{PL16} more quickly and allowing output control signal S_{3T} to be pulled down quicker. Level shifter 400 is able to flip faster, so the downstream transistors controlled by output control signal S_{3T} also switch faster. In testing using an input upper rail V_{CCA} equal to 0.8V and an output upper

rail V_{CCB} equal to 3.3V using weak process models and 130°C, the use of the pull-up circuits 404 improved propagation delay, T_{PD} , from 15 ns to 14 ns. Using the same process conditions for an input upper rail V_{CCA} equal to 1.65 V and an output upper rail V_{CCB} equal to 3.0 V, T_{PD} improved from 3.48 ns to 3.19 ns. This improvement is critical for achieving a data rate of 500 Mbps.

[0056] FIG. 5B is a view of a larger portion of the graph shown in FIG. 5A, but without output control signal S_{2T} , in order to illustrate the increased amplitude of V_{OUT} that results from the use of the added helper transistors. As shown in FIG. 5B, using the pull-up circuits 404, output control signal S_{3T} swings higher. As an effect of the higher swing of output control signal S_{3T} , V_{OUT} also swings higher. As described hereinabove, when upper rail V_{CCB} is 3.0 V, the output high voltage should not drop below 2.3 V. In a test for operation at a data rate of 500 Mbps with $V_{CCA}=1.65$ V, $V_{CCB}=3.0$ V, Weak, 130° C, with no pull-up circuits 404, the high level of V_{OUT} was 1.49 V, which is less than the required high voltage of 2.3 V at this level. In contrast, when pull-up circuits 404 were added to the circuit, the high level of V_{OUT} was 2.54 V, which is greater than the required high voltage of 2.3 V. The addition of helper transistors thus allows the level shifter to provide the necessary voltage levels for proper operation. This capability extends across the range of support input and output voltages.

[0057] The described level shifter with NMOS helper transistors is advantageous since it provides a boost to the level shifter output that adjusts with the input and output voltage levels. When the input signal is at a low voltage level compared to the output voltage level, then the NMOS pull-ups provide very little help to the PMOS transistors, which is desirable since the PMOS-to-NMOS ratio is already skewed low. However, when the input signal voltage rail becomes larger, the NMOS pull-ups provide more drive current to pull-up the output signal, which greatly improves the transient response of the level shifter. With the low skewed PMOS-to-NMOS ratio, this extra boost allows the level shifter to provide a good response time across a wide voltage supply range for both input and output levels. In addition, the active pull-ups do not contribute additional leakage current to the design like the use of passive resistors described hereinabove.

[0058] FIG. 6 depicts a voltage translator 600 according to the described embodiments, which is generally a reproduction of the separate circuits described hereinabove, but is provided to give an overview of the various circuits described herein. In this description, references to NMOS and PMOS transistors are used in a generic sense, so these transistors are referred to as metal

oxide silicon devices, even though most gates are actually made of polysilicon and other dielectrics besides oxide can be used. Variations to NMOS and PMOS transistors, whether currently known or unknown are covered by these terms.

[0059] Modifications are possible in the described embodiments, and other embodiments are possible, within the scope of the claims.

CLAIMS

What is claimed is:

1. A level shifter comprising:

a level-shifting circuit coupled to receive first and second input control signals and to provide an output control signal, the level-shifting circuit comprising a first P-type metal oxide silicon (PMOS) transistor and a second PMOS transistor, a first N-type metal oxide silicon (NMOS) transistor and a second NMOS transistor;

a third NMOS transistor coupled between an upper rail in a first voltage domain and the drain of the first PMOS transistor, the gate of the third NMOS transistor being controlled by the first input control signal; and

a fourth NMOS transistor coupled between the upper rail and the drain of the second PMOS transistor, the gate of the fourth NMOS transistor being controlled by the second input control signal.

2. The level shifter of claim 1, further comprising:

a fifth NMOS transistor coupled in parallel with the third NMOS transistor between the upper rail and the drain of the first PMOS transistor, the gate of the fifth NMOS transistor being controlled by the first input control signal; and

a sixth NMOS transistor coupled in parallel with the fourth NMOS transistor between the upper rail and the drain of the second PMOS transistor, the gate of the sixth NMOS transistor being controlled by the second input control signal;

the fifth and the sixth NMOS transistors having a first threshold voltage and the first and second PMOS transistors and the first, second, third and fourth NMOS transistors having a second threshold voltage that is lower than the first threshold voltage.

3. The level shifter of claim 2 further comprising a seventh NMOS transistor coupled between the respective sources of the first and second NMOS transistors and the lower rail, the gate of the seventh NMOS transistor receiving an enable signal.

4. The level shifter of claim 3, wherein an output control signal of the level shifter is taken from a point between the drain of the second PMOS transistor and the drain of the second NMOS transistor.

5. The level shifter of claim 1 wherein:

the first PMOS transistor is coupled in series with the first NMOS transistor between the upper rail and a lower rail;

the second PMOS transistor is coupled in series with the second NMOS transistor between the upper rail and the lower rail;

a drain of the first PMOS transistor is coupled to the gate of the second PMOS transistor and a drain of the second PMOS transistor and coupled to the gate of the first PMOS transistor; and

the gate of the first NMOS transistor is controlled by the second input control signal and the gate of the second NMOS transistor is controlled by the first input control signal.

6. The level shifter of claim 1, wherein the first input control signal and the second input control signal are provided by a circuit operating in a second voltage domain.

7. A voltage translator coupled to translate an input signal received in a first voltage domain to an output signal provided in a second voltage domain, wherein each of the first and second voltage domains can span a wide range of low voltages, the voltage translator comprising:

an input buffer coupled to receive the input signal and to provide a first input control signal and a second input control signal, the input buffer operating in the first voltage domain;

a level shifter coupled to receive the first and second input control signals and to provide an output control signal;

a gate control circuit coupled to receive the first and second input control signals and the output control signal and to provide a first gate control signal and a second gate control signal; and

an output buffer coupled to receive the first gate control signal and the second gate control signal and to provide the output signal, wherein the level shifter, the gate control circuit and the output buffer each operate in the second voltage domain,

the level shifter comprising:

a level-shifting circuit comprising a first P-type metal oxide silicon (PMOS) transistor and a second PMOS transistor, a first N-type metal oxide silicon (NMOS) transistor and a second NMOS transistor;

a third NMOS transistor coupled between an upper rail and the drain of the first PMOS transistor, the gate of the third NMOS transistor being controlled by the first input control signal; and

a fourth NMOS transistor coupled between the upper rail and the drain of the second PMOS transistor, the gate of the fourth NMOS transistor being controlled by the second input control signal.

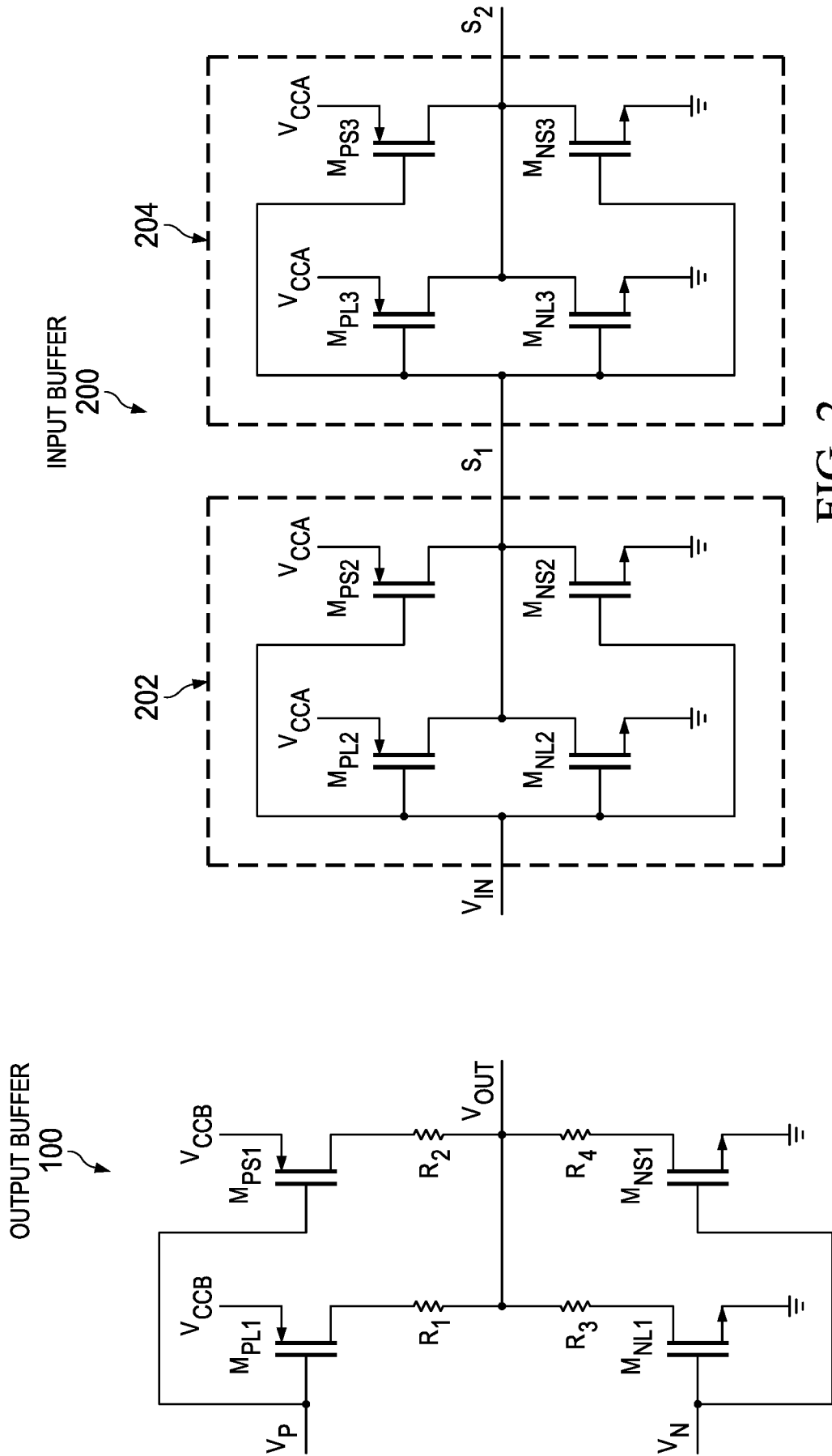


FIG. 1

FIG. 2

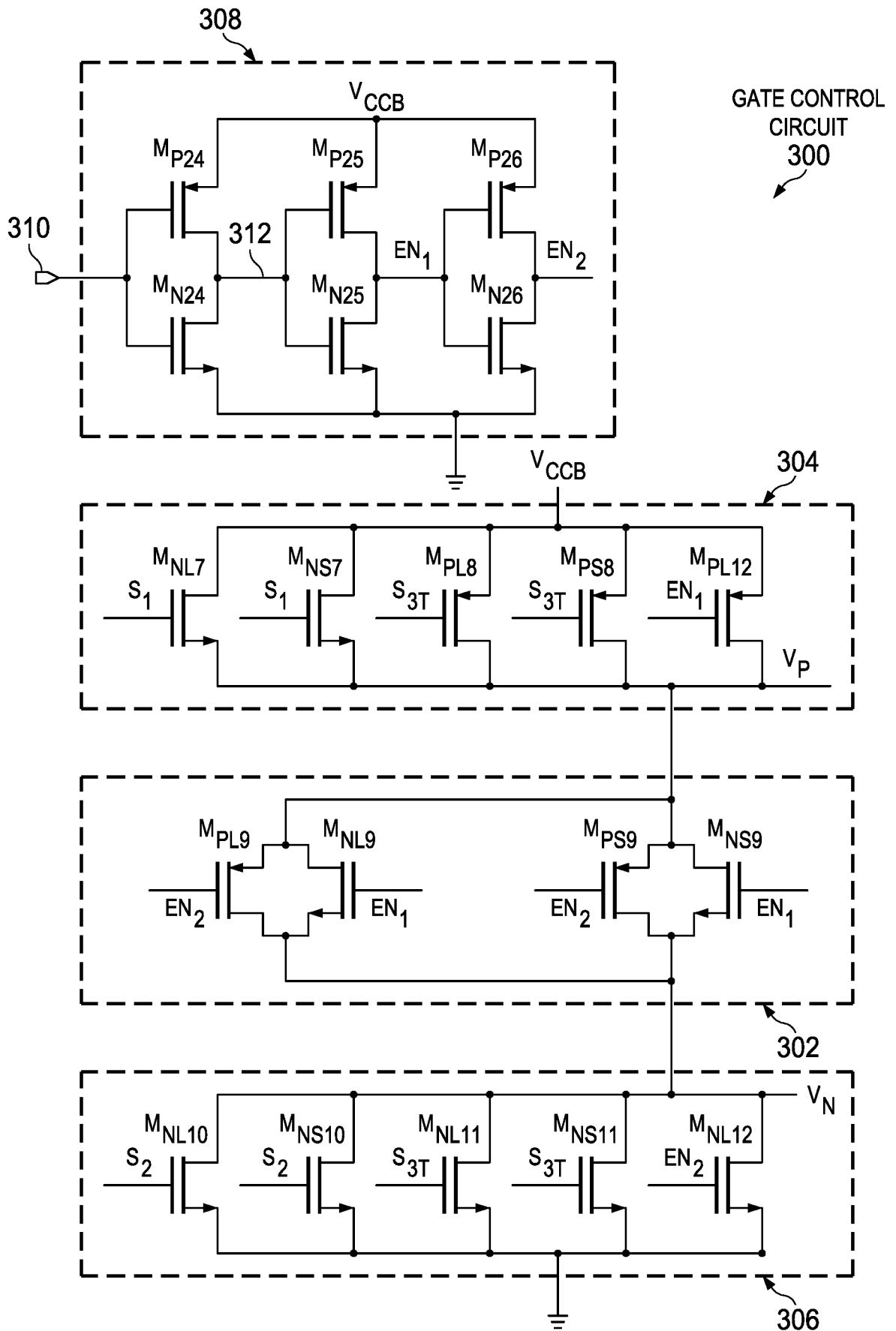


FIG. 3

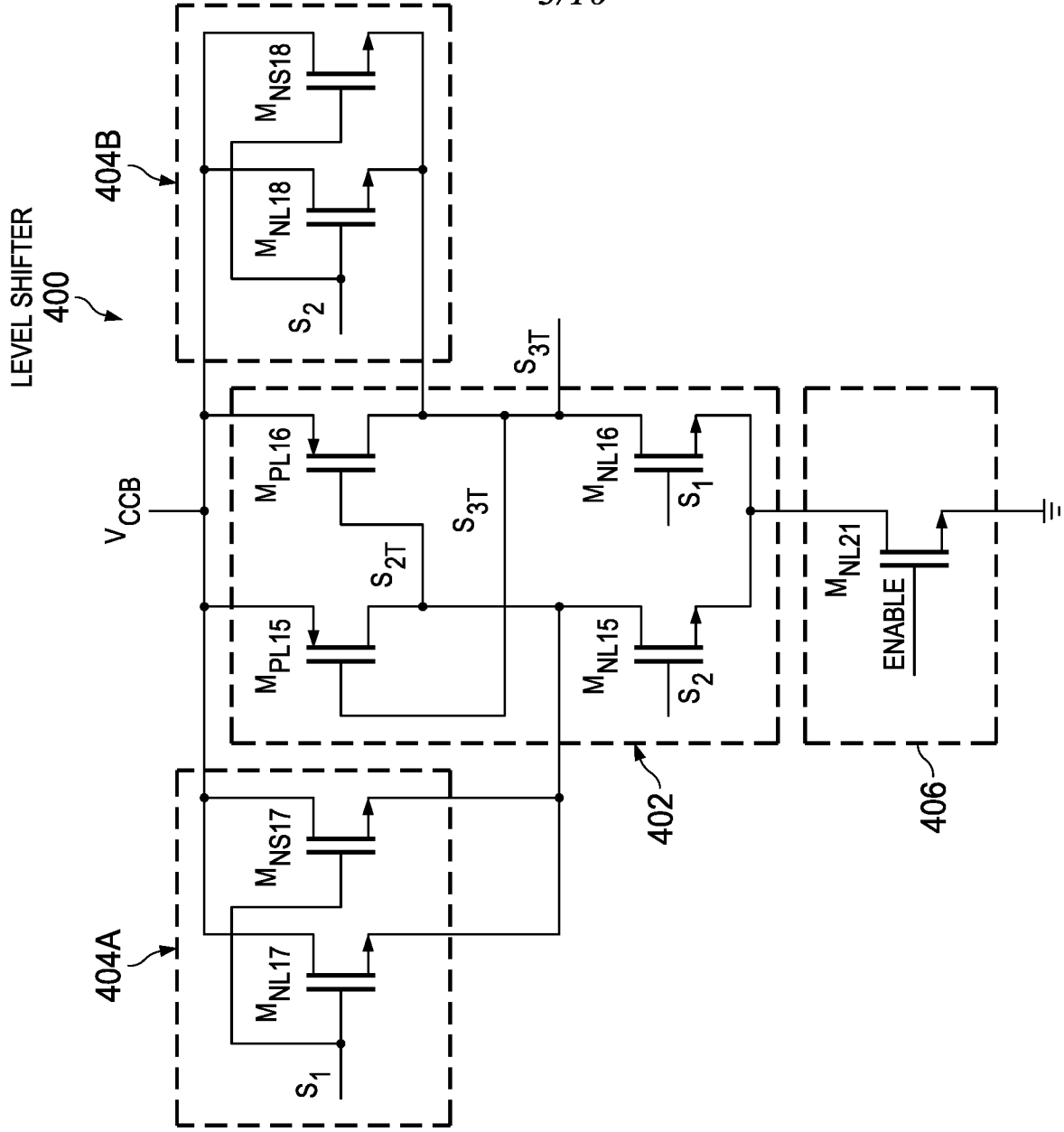


FIG. 4

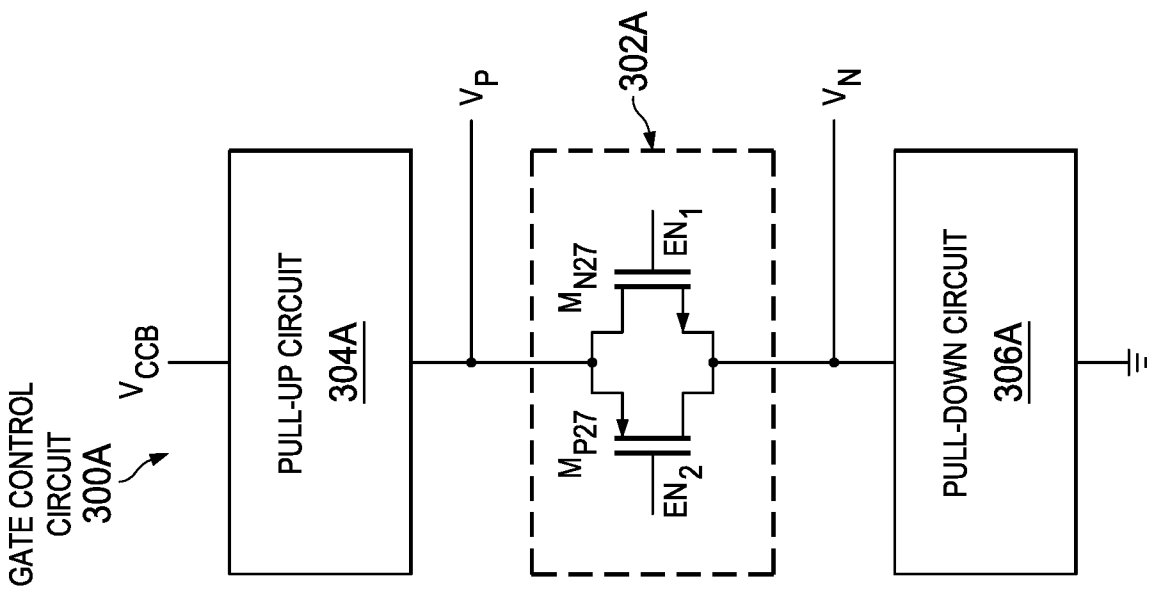


FIG. 3A

FIG. 5A

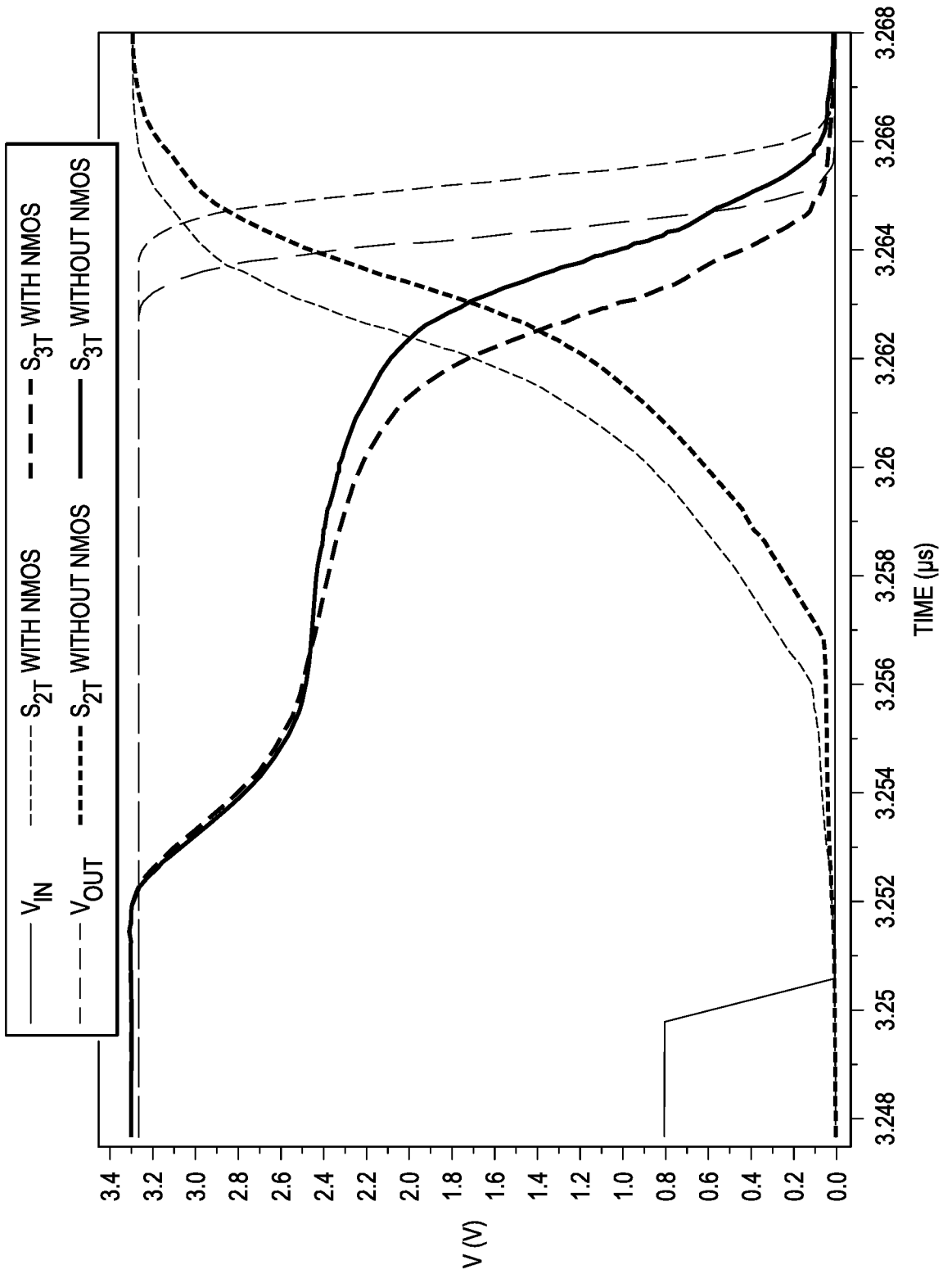
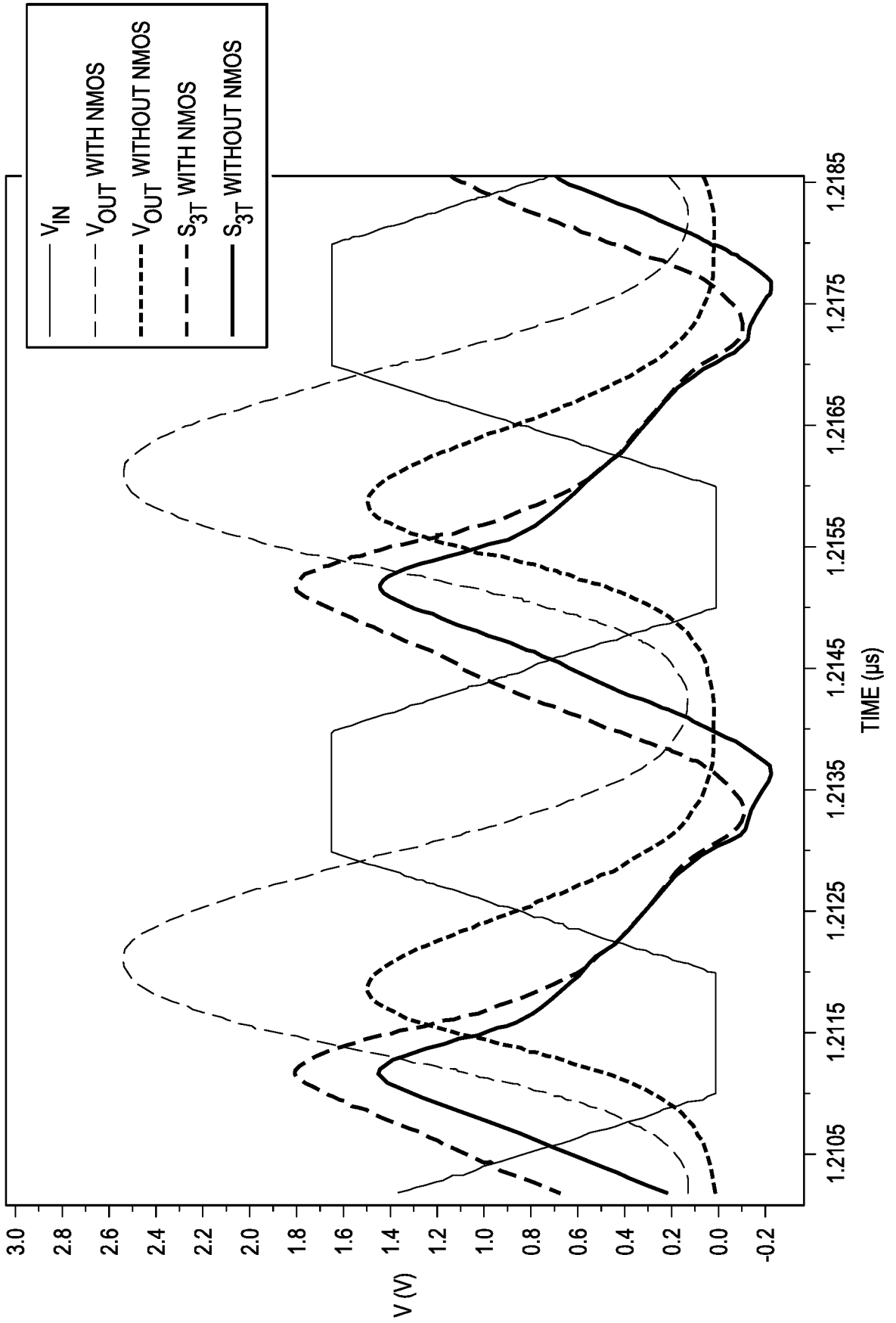


FIG. 5B



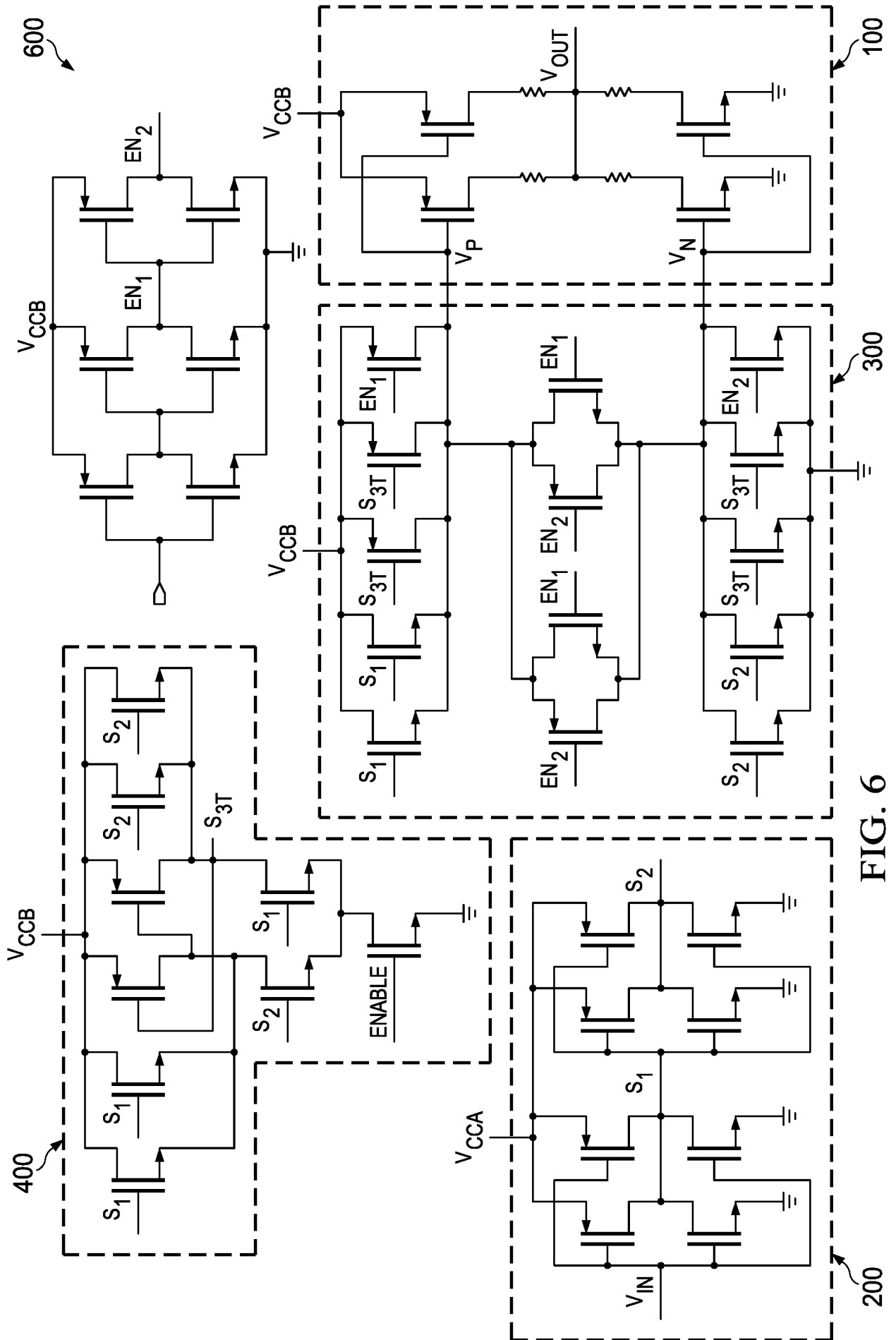


FIG. 6

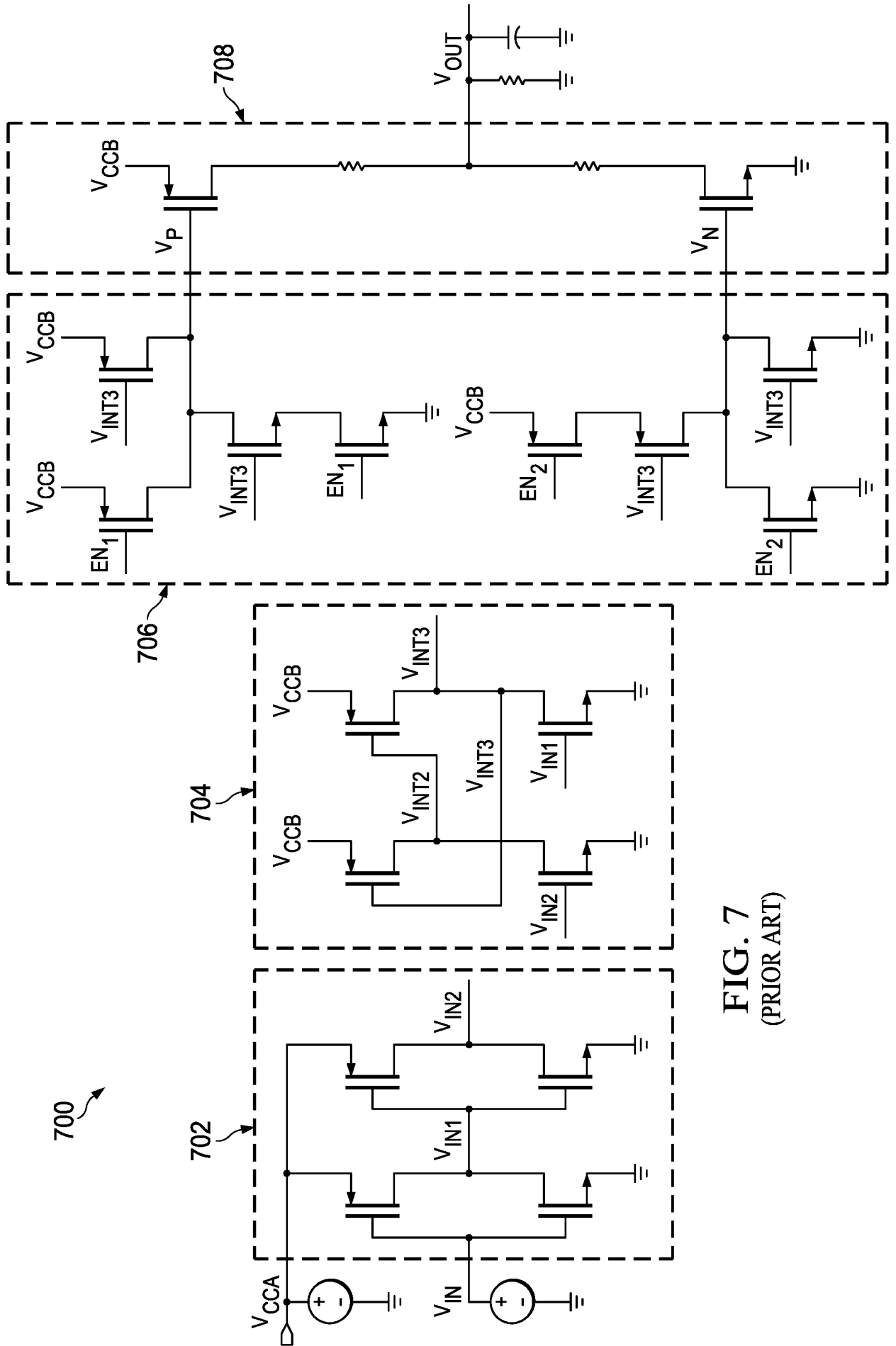
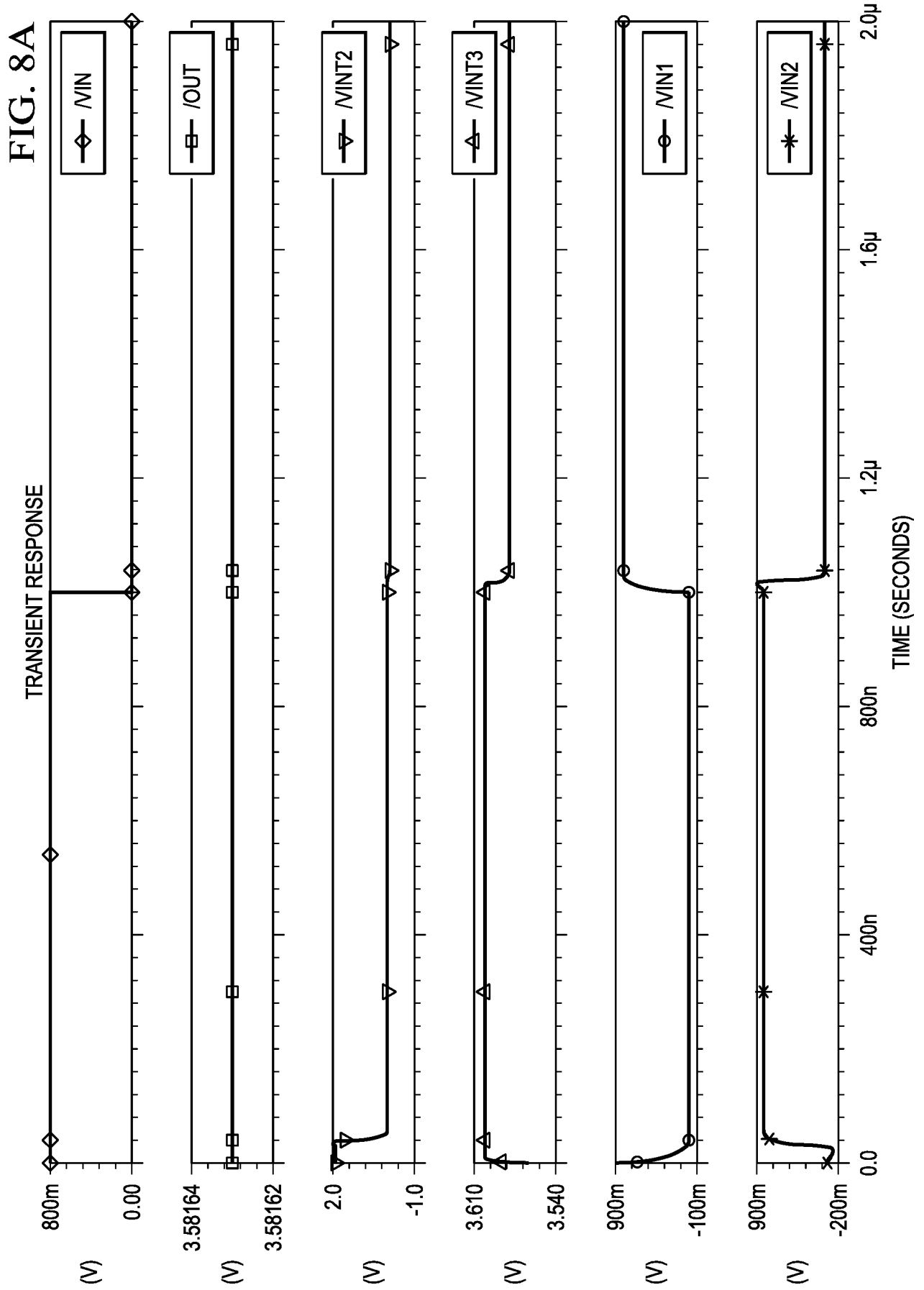
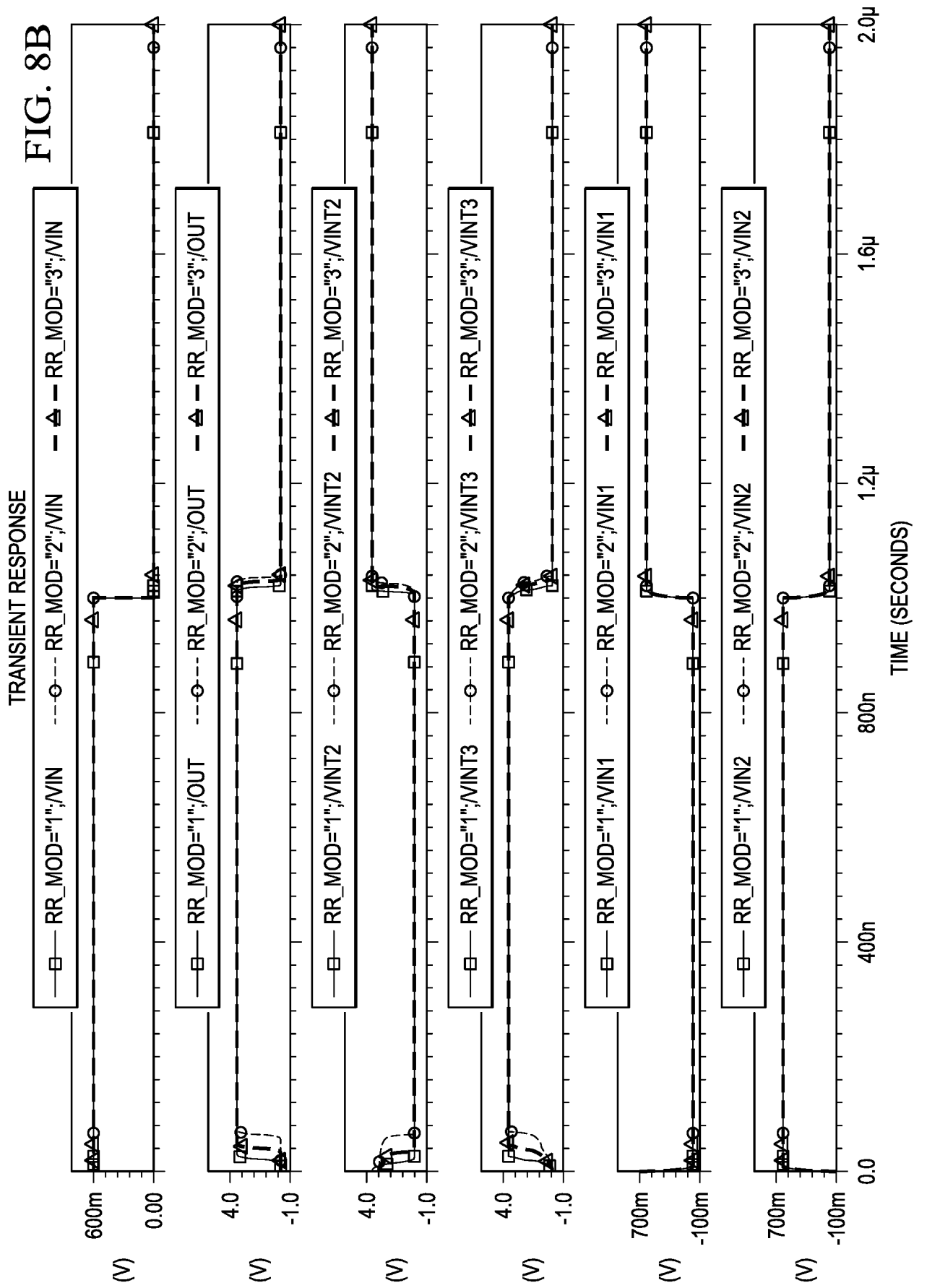


FIG. 7
(PRIOR ART)





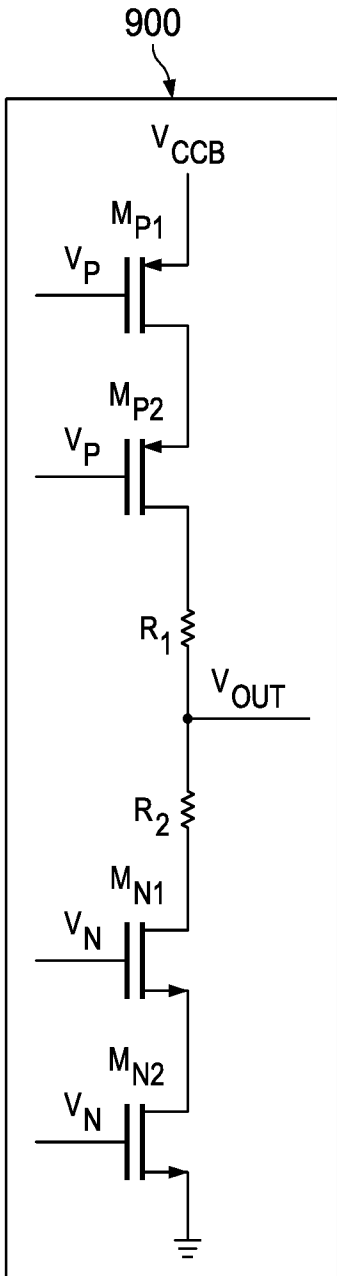


FIG. 9

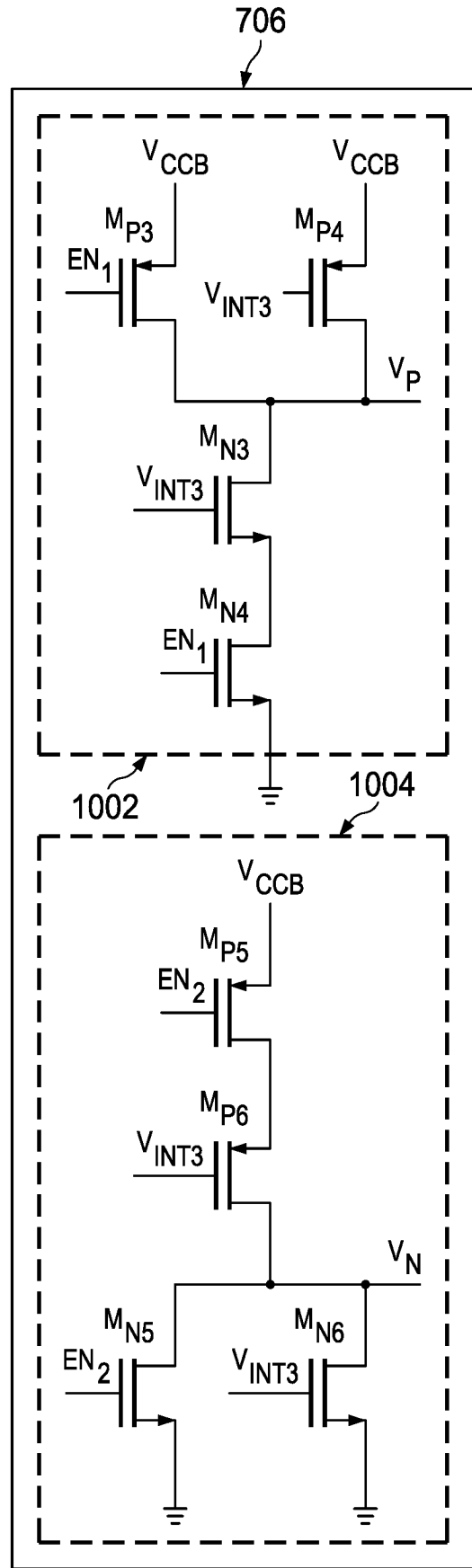


FIG. 10
(PRIOR ART)

INTERNATIONAL SEARCH REPORT

International application No.

PCT/US 2018/040056

A. CLASSIFICATION OF SUBJECT MATTER		
<i>H03K 19/088 (2006.01)</i>		
According to International Patent Classification (IPC) or to both national classification and IPC		
B. FIELDS SEARCHED		
Minimum documentation searched (classification system followed by classification symbols)		
H03K 19/00-19/088, 19/0185, 5/00-5/22, H02M 5/00-5/293, H03L 5/00		
Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched		
Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)		
PatSearch (RUPTO internal), Esp@cenet, PAJ, USPTO, Information Retrieval System of FIPS		
C. DOCUMENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	US 2014/0266385 A1 (FREESCALE SEMICONDUCTOR, INC) 18.09.2014	1-7
A	US 6445210 B2 (MATSUSHITA ELECTRIC INDUSTRIAL CO., LTD.) 03.09.2002	1-7
A	US 6940317 B2 (FUJITSU LIMITED) 06.09.2005	1-7
A	US 2014/0300188 A1 (NEP B.V.) 09.10.2014	1-7
<input type="checkbox"/> Further documents are listed in the continuation of Box C. <input type="checkbox"/> See patent family annex.		
* Special categories of cited documents:		
“A”	document defining the general state of the art which is not considered to be of particular relevance	“T” later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
“E”	earlier document but published on or after the international filing date	“X” document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
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“O”	document referring to an oral disclosure, use, exhibition or other means	“&” document member of the same patent family
“P”	document published prior to the international filing date but later than the priority date claimed	
Date of the actual completion of the international search		Date of mailing of the international search report
16 October 2018 (16.10.2018)		25 October 2018 (25.10.2018)
Name and mailing address of the ISA/RU: Federal Institute of Industrial Property, Berezhkovskaya nab., 30-1, Moscow, G-59, GSP-3, Russia, 125993 Facsimile No: (8-495) 531-63-18, (8-499) 243-33-37		Authorized officer M. Smirnov Telephone No. (495)531-64-81